AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A plasma processing apparatus, comprising:

a gas nozzle ~~gas supply means~~ for supplying a gas including a reactant gas to an interior of a chamber;

pressure control means for controlling an internal pressure of the chamber;

plasma generation means for generating a plasma of the gas in the interior of the chamber;

a susceptor, installed in a lower portion of the interior of the chamber, for supporting a substrate to be processed;

a wall surface protecting member, formed in a cylindrical form and provided in the interior of the chamber, for preventing adhesion of a plasma processing-associated product onto an inner wall surface of the chamber,

wherein the chamber includes a chamber step portion, provided to the inner wall surface of the chamber, for supporting the wall surface protecting member from below to cover the inner wall surface of the chamber located above the susceptor,

wherein the wall surface protecting member has a plurality of projections, provided on an outer wall surface and in a lower end portion of the wall surface protecting member, for contacting, by point contact, the inner wall surface of the chamber and the chamber step portion,

wherein the plurality of projections provided in the lower end portion of the wall surface protecting member extends along an axial direction of the wall surface protecting member, ~~and~~

wherein the wall surface protecting member is supported in the chamber by the point contact,

wherein the gas nozzle has a gas pipe and a nozzle tip,

the gas pipe is extended upward from lower site of the chamber within a wall of the chamber or between the wall surface protecting member and the chamber, and

the nozzle tip is detachable from the gas pipe and installed while passing through a hole provided in the wall surface protecting member.

2. (Canceled)

3. (Canceled)

4. (Previously Presented) The plasma processing apparatus according to claim 1 or 13, wherein the wall surface protecting member is made of a ceramic.

5. (Previously Presented) The plasma processing apparatus according to claim 1 or 13, wherein the wall surface protecting member is made of a metal.

6. (Previously Presented) The plasma processing apparatus according to claim 5, wherein the metal is aluminum.

7. (Previously Presented) The plasma processing apparatus according to claim 5, wherein the wall surface protecting member has a surface oxidized.

8. (Previously Presented) The plasma processing apparatus according to claim 1 or 13, wherein the wall surface protecting member has a surface roughened.

9. (Canceled)

10. (Canceled)

11. (Previously Presented) The plasma processing apparatus according to claim 1 or 13, further comprising:

heating means for heating a wall surface of the chamber.

12. (Previously Presented) The plasma processing apparatus according to claim 11, wherein the heating means heats the wall surface of the chamber to 100°C or higher.

13. (Previously Presented) The plasma processing apparatus according to claim 1, wherein the plurality of projections provided on the outer wall surface of the wall surface protecting member is provided at a lower portion of the wall surface protecting member.